## **NRVBB1060**, **NRVBB1060W1**

## **Switch-mode Power Rectifier**

This switch-mode power rectifier uses the Schottky Barrier principle with a platinum barrier metal. This state-of-the-art device has the following features:

#### **Features**

- Low Forward Voltage
- 175°C Operating Junction Temperature
- Low Power Loss/High Efficiency
- High Surge Capacity
- For Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- This is a Pb-Free Device

#### **Applications**

- Power Supply Output Rectification
- Power Management

#### **Mechanical Characteristics**

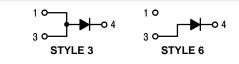
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.7 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



#### ON Semiconductor®

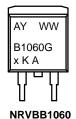
www.onsemi.com

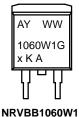
### **SCHOTTKY BARRIER** RECTIFIER 10 AMPERES, 60 VOLTS





#### **MARKING DIAGRAMS**





= Assembly Location Α

= Year WW = Work Week G = Pb-Free Package xKA = Diode Polarity = N or A

#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NRVBB1060T4G	D <sup>2</sup> PAK (Pb-Free)	800/Tape & Reel
NRVBB1060W1T4G	D <sup>2</sup> PAK (Pb-Free)	800/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

### **NRVBB1060, NRVBB1060W1**

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	60	V
Average Rectified Forward Current (Rated V <sub>R</sub> ) T <sub>C</sub> = 133°C	I <sub>F(AV)</sub>	10	А
Peak Repetitive Forward Current (Rated V <sub>R</sub> , Square Wave, 20 kHz) T <sub>C</sub> = 133°C	I <sub>FRM</sub>	20	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I <sub>FSM</sub>	150	А
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I <sub>RRM</sub>	0.5	А
Operating Junction Temperature (Note 1)	TJ	-65 to +175	°C
Storage Temperature	T <sub>stg</sub>	- 65 to +175	°C
Voltage Rate of Change (Rated V <sub>R</sub> )	dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction–to–Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

#### THERMAL CHARACTERISTICS

THERWAL CHARACTERISTICS			
Maximum Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	2.0	°C/W
Maximum Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	60	°C/W
ELECTRICAL CHARACTERISTICS			
Maximum Instantaneous Forward Voltage (Note 2) ( $i_F = 10 \text{ Amps}$ , $T_C = 125^{\circ}\text{C}$ ) ( $i_F = 10 \text{ Amps}$ , $T_C = 25^{\circ}\text{C}$ ) ( $i_F = 20 \text{ Amps}$ , $T_C = 125^{\circ}\text{C}$ ) ( $i_F = 20 \text{ Amps}$ , $T_C = 25^{\circ}\text{C}$ )	VF	0.7 0.8 0.85 0.95	V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_C = 125^{\circ}C$ ) (Rated dc Voltage, $T_C = 25^{\circ}C$ )	İR	25 0.10	mA

<sup>2.</sup> Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

### NRVBB1060, NRVBB1060W1

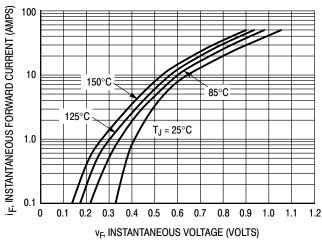
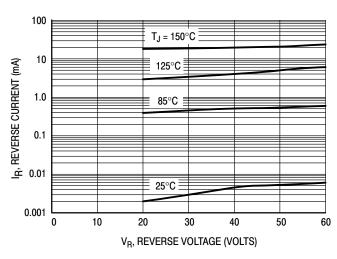


Figure 1. Typical Forward Voltage



**Figure 2. Typical Reverse Current** 

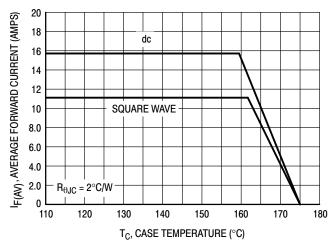


Figure 3. Current Derating, Case

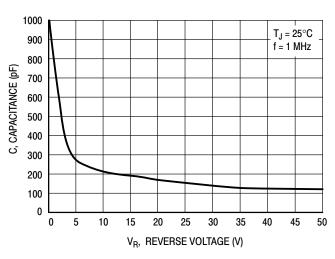


Figure 4. Typical Capacitance

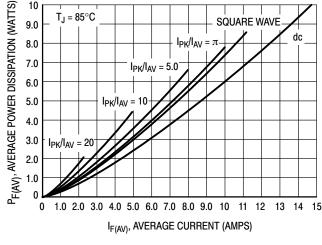


Figure 5. Typical Forward Power Dissipation

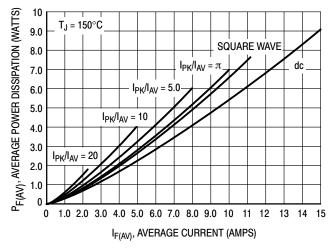


Figure 6. Typical Forward Power Dissipation

### NRVBB1060, NRVBB1060W1

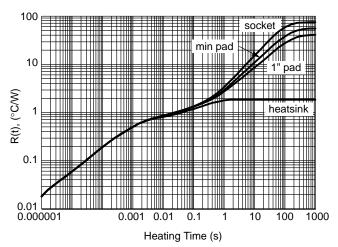


Figure 7. Single-Pulse Transient Response Curves, Various Mounting Conditions

### **MECHANICAL CASE OUTLINE**

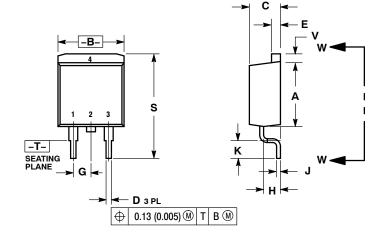




D<sup>2</sup>PAK 3 CASE 418B-04 **ISSUE L** 

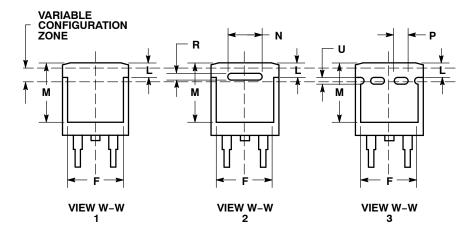
**DATE 17 FEB 2015** 

#### SCALE 1:1



- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: INCH.
- 3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.340	0.380	8.64	9.65
В	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
Е	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
Н	0.080	0.110	2.03	2.79
7	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
М	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
Р	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
٧	0.045	0.055	1.14	1.40



STYLE 1: PIN 1. BASE 2. COLLECTOR
3. EMITTER
4. COLLECTOR STYLE 2: PIN 1. GATE 2. DRAIN

3. SOURCE 4. DRAIN

STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE 4. CATHODE

STYLE 4:

PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. ANODE

STYLE 6: PIN 1. NO CONNECT
2. CATHODE
3. ANODE
4. CATHODE

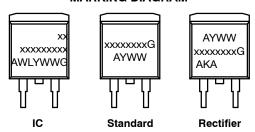
#### **MARKING INFORMATION AND FOOTPRINT ON PAGE 2**

DOCUMENT NUMBER:	98ASB42761B	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	D <sup>2</sup> PAK 3		PAGE 1 OF 2

ON Semiconductor and (III) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

**DATE 17 FEB 2015** 

# GENERIC MARKING DIAGRAM\*



xx = Specific Device Code A = Assembly Location

 WL
 = Wafer Lot

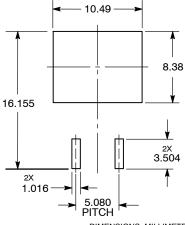
 Y
 = Year

 WW
 = Work Week

 G
 = Pb-Free Package

 AKA
 = Polarity Indicator

#### **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

DOCUMENT NUMBER:	98ASB42761B	Electronic versions are uncontrolled except when accessed directly from the Document Reposit Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	D <sup>2</sup> PAK 3		PAGE 2 OF 2

ON Semiconductor and at a trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot " ■", may or may not be present.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT: Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative